

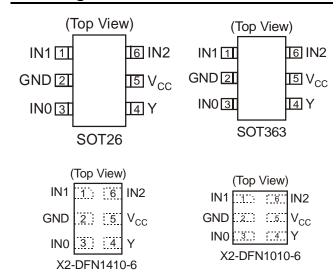
Description

The 74LVC1G57 is a single 3-input positive configurable multiple function gate with a standard push-pull output. The output state is determined by eight patterns of 3-bit input. The user can chose the logic functions AND, OR, NAND, NOR, XNOR, inverter or non-inverting buffer. All inputs can be connected to ground or Vcc as required. The device is designed for operation with a power supply range of 1.65V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using IOFF. The IOFF circuitry disables the output preventing damaging current backflow when the device is powered down. The user is reminded that the device can simulate several types of logic gates but may respond differently due to the Schmitt action at the inputs.

Features

- Wide Supply Voltage Range from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- · CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115-A)
 - 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- SOT26, SOT363, X2-DFN1410-6, and X2-DFN1010-6: Available in "Green" Molding Compound (no Br, Sb)
 - Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
 - Halogen and Antimony Free. "Green" Device (Note 3)

Pin Assignments



Applications

- Voltage Level Shifting
- General Purpose Logic
- Power Down Signal Isolation
- · Wide array of products such as:
 - PCs, networking, notebooks, netbooks, PDAs
 - Computer peripherals, hard drives, CD/DVD ROM
 - TV, DVD, DVR, set top box
 - Cell Phones, Personal Navigation / GPS
 - MP3 players ,Cameras, Video Recorders

Notes:

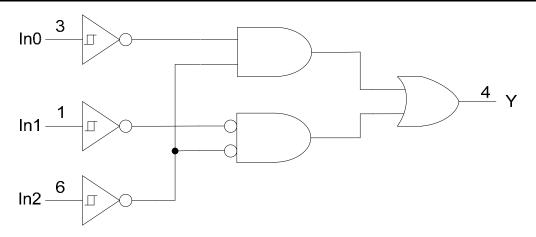
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



Pin Descriptions

Pin Name	Function
IN1	Data Input
GND	Ground
IN0	Data Input
Υ	Data Output
V _{CC}	Supply Voltage
IN2	Data Input

Logic Diagram

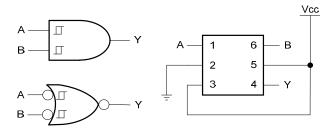


Function Table

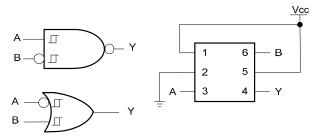
	Inputs	Output	
IN2	IN1	IN0	Y
L	L	L	Н
L	L	Н	L
L	Н	L	Н
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	Н
Н	Н	Н	Н



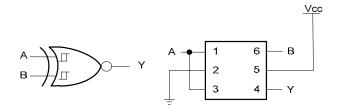
Logic Configurations



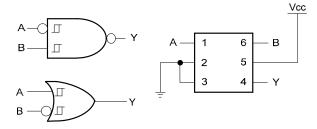
Configuration 1
2-Input AND Gate
2-Input NOR Gate with Both Inputs Inverted



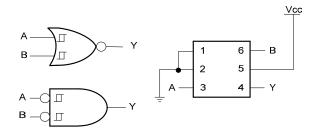
Configuration 3
2-Input NAND Gate with B Input Inverted
2-Input OR Gate with A Input Inverted



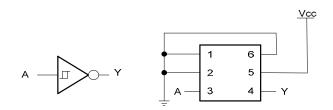
Configuration 5
2-Input XNOR Gate



Configuration 2
2-Input NAND Gate with A Input Inverted
2-Input OR Gate with B input Inverted



Configuration 4
2-Input NOR Gate
2-Input AND Gate with Both Inputs Inverted



Configuration 6 Inverter

Function Selection Table							
Logic Function	Configuration						
2-input AND	1						
2-input AND with both inputs inverted	4						
2-input NAND with inverted input	2, 3						
2-input OR with inverted input	2, 3						
2-input NOR	4						
2-input NOR with both inputs inverted	1						
2-input XNOR	5						
1-input INVERTER	6						



Absolute Maximum Ratings (Note 4)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +6.5	V
VI	Input Voltage Range	-0.5 to +6.5	V
Vo	Voltage applied to output in high impedance or I _{OFF} state	-0.5 to +6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current V _I <0	-50	mA
lok	Output Clamp Current	-50	mA
lo	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

Recommended Operating Conditions (Note 5)

Symbol		Parameter	Min	Max	Unit
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	On anoting Waltern	Operating	1.65	5.5	V
V _{CC}	Operating Voltage	Data retention only	1.5		V
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	Vcc	V
		V _{CC} = 1.65V		-4	
		V _{CC} = 2.3V		-8	
Іон	High-level output current			-16	mA
		$V_{CC} = 3V$		-24	
		V _{CC} = 4.5V		-32	
		V _{CC} = 1.65V		4	
		V _{CC} = 2.3V		8	
I _{OL}	Low-level output current			16	mA
		$V_{CC} = 3V$		24	
		V _{CC} = 4.5V		32	
		V _{CC} = 1.8V ± 0.15V, 2.5V ± 0.2V		20	
Δt/ΔV	Input transition rise or fall rate $V_{CC} = 3.3V \pm 0.3V$			10	ns/V
		V _{CC} = 5V ± 0.5V		5	
T _A	Operating free-air temperature		-40	+125	°C

Notes: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics $T_A = -40^{\circ}\text{C}$ to +85°C (All typical values are at $V_{CC} = 3.3V$, $T_A = +25^{\circ}\text{C}$)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V_{T+}	Positive-going input threshold voltage		3V	1.50		2.00	
			4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.72	
			2.3V	0.58		1.00	
V_{T-}	Negative-going input		3V	0.80		1.30	
	threshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.40		0.80	
ΔV_T	Hysteresis		3V	0.35		1.00	
	(V _{T+} - V _{T-)}		4.5V	0.55		1.10	
			5.5V	0.60		1.20	
		I _{OH} = -100μA	1.65V to 5.5V	V _{CC} -0.1			
		$I_{OH} = -4mA$	1.65V	1.2			
V	Pale Lavad Outroot Vallana	$I_{OH} = -8mA$	2.3V	1.9			\ /
V_{OH}	High Level Output Voltage	I _{OH} = -16mA	0)/	2.4			V
		I _{OH} = -24mA	3V	2.3			
		I _{OH} = -32mA	4.5V	3.8			
		$I_{OL} = 100 \mu A$	1.65V to 5.5V			0.1	
		I _{OL} = 4mA	1.65V			0.45	
V	LP ob Toward London Maltana	I _{OL} = 8mA	2.3V			0.3	
V_{OL}	High-level Input Voltage	I _{OL} = 16mA	0)/			0.4	V
		$I_{OL} = 24mA$	3V			0.55	
		$I_{OL} = 32mA$	4.5V			0.55	
lı	Input Current	V _I = 5.5V or GND	0 to 5.5V			±5	μΑ
I _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 10	μΑ
Icc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			10	μΑ
Δl _{CC}	Additional Supply Current	One input at V _{CC} -0.6V Other inputs at V _{CC} or GND	3V to 5.5V			500	μА



Electrical Characteristics $T_A = -40$ °C to +125°C (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit
			1.65V	0.70		1.20	
			2.3V	1.11		1.60	
V_{T+}	Positive-going input threshold voltage		3V	1.50		2.00	
	Timeshold voltage		4.5V	2.16		2.74	
			5.5V	2.61		3.33	
			1.65V	0.30		0.75	
	No series and an insert		2.3V	0.58		1.03	
V _T -	Negative-going input threshold voltage		3V	0.80		1.33	
	tilleshold voltage		4.5V	1.21		1.95	
			5.5V	1.45		2.35	
			1.65V	0.30		0.62	
			2.3V	0.37		0.80	
ΔV_T	Hysteresis (V _{T+} - V _{T-)}		3V	0.32		1.00	
	(4.5V	0.50		1.20	
			5.5V	0.55		1.40	
	Libert Control Office of Marketine	$I_{OH} = -100\mu A$	1.65V to 5.5V	V _{CC} -0.1			
		$I_{OH} = -4mA$	1.65V	0.95			
		$I_{OH} = -8mA$	2.3V	1.7			V
V _{OH}	High Level Output Voltage	I _{OH} = -16mA	2) /	1.9			
		I _{OH} = -24mA	3V	2.0			
		I _{OH} = -32mA	4.5V	3.4			
		I _{OL} = 100μA	1.65V to 5.5V			0.1	
		$I_{OL} = 4mA$	1.65 V			0.7	
	Link lavel land Make as	I _{OL} = 8mA	2.3V			0.45	V
V _{OL}	High-level Input Voltage	I _{OL} = 16mA	2)./			0.6	V
		$I_{OL} = 24mA$	3V			0.8	
		I _{OL} = 32mA	4.5V			0.8	
l _l	Input Current	V _I = 5.5 V or GND	0 to 5.5V			± 100	μA
l _{OFF}	Power Down Leakage Current	V_I or $V_O = 5.5V$	0			± 200	μA
Icc	Supply Current	V _I = 5.5V of GND I _O =0	1.65V to 5.5V			200	μΑ
ΔI _{CC}	Additional Supply Current	One input at V _{CC} –0.6V Other inputs at V _{CC} or GND	3V to 5.5V			5000	μΑ



Package Characteristics (All typical values are at $V_{CC} = 3.3V$, $T_A = +25$ °C)

Symbol	Parameter	Test Conditions	V _{CC}	Min	Тур.	Max	Unit	
CI	Input Capacitance	$V_I = V_{CC} - \text{or GND}$	3.3		3.5		pF	
		SOT26			204			
	Thermal Resistance Junction-	SOT363	(Note 6)		371		00.00	
θ _{JA}	to-Ambient	X2-DFN1410-6			430		°C/W	
		X2-DFN1010-6			510			
	SOT26			52				
	Thermal Resistance Junction-	SOT363	(Note 6)		143		°C/W	
θ _{JC}	to-Case	X2-DFN1410-6			190			
		X2-DFN1010-6			250			

Notes:

Switching Characteristics

 $T_A = -40$ °C to +85°C, $C_L = 30$ or 50pF as noted (see Figure 1)

From Parameter (terret)	TO (OUTPUT)		: 1.8V .15V		= 2.5V).2V	~ ~	: 3.3V).3V	V _{CC}	= 5V .5V	Unit	
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Υ	1.0	14.4	0.7	8.3	0.7	6.3	0.7	5.1	ns

 $T_A = -40$ °C to +125°C, $C_L = 30$ or 50pF as noted (see Figure 1)

Parameter	From			V _{CC} = 1.8V ± 0.15V		V _{CC} = 2.5V ± 0.2V		V _{CC} = 3.3V ± 0.3V		V _{CC} = 5V ± 0.5V	
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pd}	Any	Υ	1.0	18.0	0.7	10.4	0.7	7.9	0.7	6.4	ns

Operating Characteristics

$T_A = +25^{\circ}C$

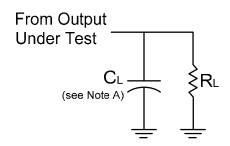
	Parameter	Test Conditions	Vcc = 1.8V Typ.	Vcc = 2.5V Typ.	Vcc = 3.3V Typ.	Vcc = 5V Typ.	Unit
C _{pd}	Power dissipation capacitance	f = 10 MHz	22	22	23	24	pF

^{6.} Test condition for SOT26, SOT363, X2-DFN1410-6 and X2-DFN1010-6: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Propagation Delay Times
Inverting and Non Inverting Outputs

Parameter Measurement Information



v	Inj	outs	V		В	
V _{CC}	VI	t _r /t _f	V _M	CL	R_L	
1.8V ±0.15V	V _{CC}	≤ 2ns	V _{CC} /2	30pF	1ΚΩ	
2.5V ±0.2V	V _{CC}	≤ 2ns	V _{CC} /2	30pF	500Ω	
3.3V ±0.3V	3V	≤ 2.5ns	1.5V	50pF	500Ω	
5V ±0.5V	V _{CC}	≤ 2.5ns	V _{CC} /2	50pF	500Ω	

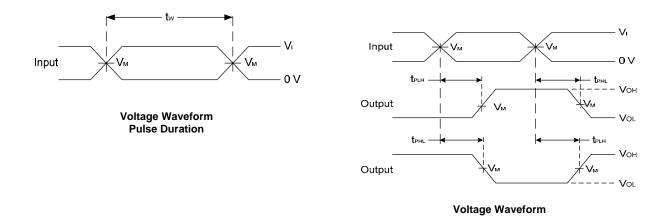


Figure 1. Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied at pulse repetition rate \leq 10 MHz
- C. Inputs are measured separately one transition per measurement
- D. t_{PLH} and t_{PHL} are the same as t_{PD}

74LVC1G57 Document number: DS35125 Rev. 4 - 2



Ordering Information

Logic Device Function Package Packing
74: Logic Prefix 57: 3-Input W6: SOT26 7: Tape & Reel

LVC: 1.65 to 5.5V Configurable DW: SOT363

Family Multiple-Function FW4: X2-DFN1010-6 1G: One gate Gate FZ4: X2-DFN1410-6

	Bester	Basks as Oak	Packaging	7" Tape and Reel	
	Device	Package Code	(Note 7)	Quantity	Part Number Suffix
9	74LVC1G57W6-7	W6	SOT26	3000/Tape & Reel	-7
9	74LVC1G57DW-7	DW	SOT363	3000/Tape & Reel	-7
9	74LVC1G57FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
9	74LVC1G57FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7

Notes: 7. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Marking Information

(1) SOT26, SOT363

5 4 6

XXYWX 2 3 XX: Identification code

Y: Year 0~9

W: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week

X: A~Z: Internal Code

Part Number	Package	Identification Code
74LVC1G57W6	SOT26	TW
74LVC1G57DW	SOT363	TW

(2) X2-DFN1010-6, X2-DFN1410-6

(Top View)

XX XX: Identification Code

 $\overline{\underline{Y}}$: Year : 0~9

Week: A~Z: 1~26 week;
 a~z: 27~52 week; z represents

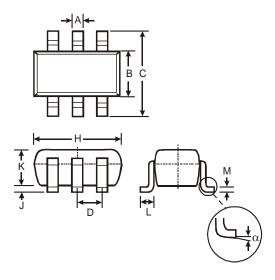
52 and 53 week \underline{X} : A~Z: Internal code

Part Number	Package	Identification Code
74LVC1G57FW4	X2-DFN1010-6	TW
74LVC1G57FZ4	X2-DFN1410-6	TW



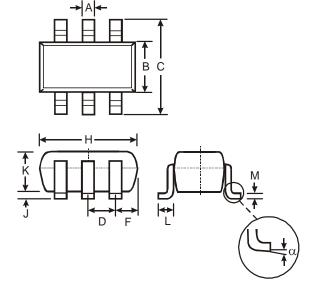
Package Outline Dimensions (All Dimensions in mm)

(1) SOT26



SOT26				
Dim	Min	Max	Тур	
Α	0.35	0.50	0.38	
В	1.50	1.70	1.60	
C	2.70	3.00	2.80	
D	_		0.95	
Η	2.90	3.10	3.00	
7	0.013	0.10	0.05	
K	1.00	1.30	1.10	
١	0.35	0.55	0.40	
М	0.10	0.20	0.15	
α	0°	8°	_	
All Dimensions in mm				

(2) SOT363

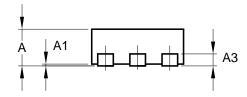


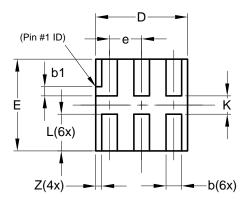
SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65	Тур		
F	0.40	0.45		
Ι	1.80	2.20		
J	0	0.10		
K	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				



Package Outline Dimensions (All Dimensions in mm)

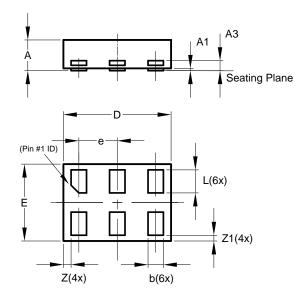
(3) X2-DFN1010-6





X2-DFN1010-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A1	0.00	0.05	0.02	
А3	_	_	0.13	
b	0.14	0.20	0.17	
b1	0.05	0.15	0.10	
D	0.95	1.05	1.00	
Е	0.95	1.05	1.00	
е	_	_	0.35	
L	0.35	0.45	0.40	
K	0.15		_	
Z	_		0.065	
All Dimensions in mm				

(4) X2-DFN1410-6

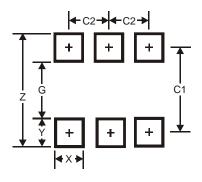


X2-DFN1410-6				
Dim	Min	Max	Тур	
Α	_	0.40	0.39	
A 1	0.00	0.05	0.02	
A3		_	0.13	
b	0.15	0.25	0.20	
D	1.35	1.45	1.40	
Е	0.95	1.05	1.00	
е		_	0.50	
L	0.25	0.35	0.30	
Z	_	_	0.10	
Z 1	0.045	0.105	0.075	
All Dimensions in mm				



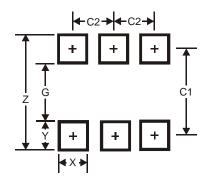
Suggest Pad Layout

(1) SOT26



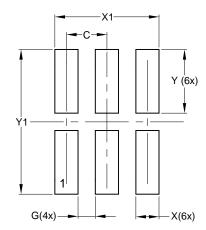
Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65

(3) X2-DFN1010-6

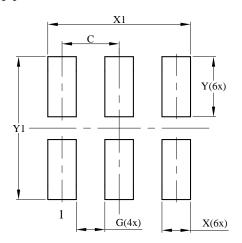


Dimensions	Value (in mm)
С	0.350
G	0.150
Х	0.200
X1	0.900
Y	0.550
Y1	1.250



Suggest Pad Layout

(4) X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Υ	0.525
Y1	1.250



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 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

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